

10/711574

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	335	DRAM and memory and cell and mask and trench and deep and capacitor and dielectric and collar and oxide	USPAT	OR	ON	2005/06/07 11:26
L2	35	DRAM and memory and cell and mask and trench and deep and capacitor and dielectric and collar and oxide and semiconductor and strip and electrode and conductive	USPAT	OR	ON	2005/06/07 11:27
L3	0	2 and (semiconductor adj strip) and (deep adj trench)	USPAT	OR	ON	2005/06/07 11:27
L4	0	1 and (semiconductor adj strip) and (deep adj trench)	USPAT	OR	ON	2005/06/07 11:27
L5	0	1 and (semiconductor adj strip) and trench	USPAT	OR	ON	2005/06/07 11:28
L6	65	1 and strip and (deep adj trench)	USPAT	OR	ON	2005/06/07 11:29
L7	35	2 and strip and (deep adj trench)	USPAT	OR	ON	2005/06/07 11:29
L8	2	2 and strip and (deep adj trench) and (patterned adj mask)	USPAT	OR	ON	2005/06/07 11:30
L9	3	1 and strip and (deep adj trench) and (patterned adj mask)	USPAT	OR	ON	2005/06/07 11:38
L10	1	("6426253").PN.	USPAT	OR	OFF	2005/06/07 11:38
L11	1	("6037194").PN.	USPAT	OR	OFF	2005/06/07 11:38
L12	1	("5945707").PN.	USPAT	OR	OFF	2005/06/07 11:38